

# BUL1102E

# High voltage fast-switching NPN power transistor

#### Features

- High voltage capability
- Very high switching speed

### Applications

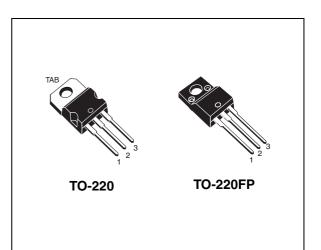
Four lamp electronic ballast for:

- 120 V mains in push-pull configuration
- 277 V mains in half bridge current feed configuration

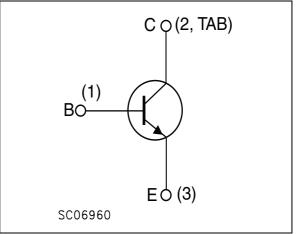
### Description

This is a high voltage fast switching NPN power transistor manufactured in multi epitaxial planar technology. It uses a cellular emitter structure with planar edge termination to enhance switching speeds while maintaining a wide RBSOA.

Thanks to an increased intermediate layer, it has an intrinsic ruggedness which enables the transistor to withstand a high collector current level during breakdown condition, without using the Transil<sup>™</sup> protection usually necessary in typical converters for lamp ballast.



#### Figure 1. Internal schematic diagram



#### Table 1. Device summary

Order codes	Marking	Package	Packaging	
BUL1102E	BUL1102E	TO-220	Tube	
BUL1102EFP	BUL1102EFP	TO-220FP	Tube	

## 1 Absolute maximum ratings

Table 2. Absolute maximum rating	gs
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Symbol	Parameter	Value	Unit
V <sub>CES</sub>	Collector-emitter voltage ( $V_{BE} = 0$ )	1100	V
V <sub>CEO</sub>	Collector-emitter voltage (I <sub>B</sub> = 0)	450	V
V <sub>EBO</sub>	Emitter-base voltage ( $I_C = 0$ )	12	V
Ι <sub>C</sub>	Collector current	4	А
I <sub>CM</sub>	Collector peak current (t <sub>P</sub> < 5 ms)	8	А
Ι <sub>Β</sub>	Base current	2	А
I <sub>BM</sub>	Base peak current (t <sub>P</sub> < 5 ms)	4	А
P <sub>TOT</sub>	BUL1102E total dissipation at $T_C = 25^{\circ}C$ BUL1102EFP total dissipation at $T_C = 25^{\circ}C$	70 30	W
V <sub>ISO</sub>	BUL1102EFP insolation withstand voltage (RMS) from all three leads to external heatsink	1500	V
T <sub>STG</sub>	Storage temperature	-65 to 150	°C
TJ	Max. operating junction temperature	150	°C

Table 3.Thermal data

Symbol	Parameter	Value	Unit
D	BUL1203E thermal resistance junction-case	1.8	°C/W
R <sub>thJC</sub>	BUL1203EFP thermal resistance junction-case	4.2	°C/W



### 2 Electrical characteristics

 $(T_J = 25 \ ^{\circ}C; \text{ unless otherwise specified})$ 

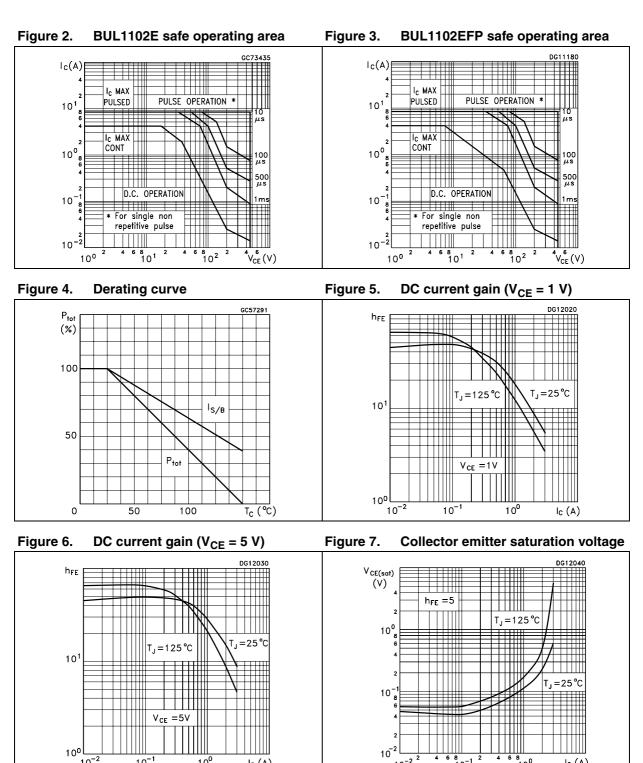
Table 4.	Electrical	characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I <sub>CES</sub>	Collector cut-off current (V <sub>BE</sub> = 0)	V <sub>CE</sub> =1100 V			100	μA
I <sub>EBO</sub>	Emitter cut-off current $(I_C = 0)$	V <sub>EB</sub> = 12 V			1	mA
V <sub>CEO(sus)</sub> <sup>(1)</sup>	Collector-emitter sustaining voltage (I <sub>B</sub> =0)	I <sub>C</sub> = 100 mA	450			V
V <sub>CE(sat)</sub> <sup>(1)</sup>	Collector-emitter saturation voltage	I <sub>C</sub> = 2 A I <sub>B</sub> =400 mA			1.5	V
V <sub>BE(sat)</sub> <sup>(1)</sup>	Base-emitter saturation voltage	I <sub>C</sub> = 2 A I <sub>B</sub> = 400 mA			1.5	V
		I <sub>C</sub> = 250 mA V <sub>CE</sub> = 5 V	35		70	
h <sub>FE</sub> <sup>(1)</sup>	DC current gain	$I_{C} = 2 A,$ $V_{CE} = 5 V$ for BUL1102E $I_{C} = 2 A$ $V_{CE} = 5 V$	12		20	
		for BUL1102EFP	12		23	
t <sub>s</sub> t <sub>f</sub>	Resistive load Storage time Fall time	$\begin{split} I_{C} &= 2.5 \text{ A} & V_{CC} &= 250 \text{ V} \\ I_{B1} &= 0.5 \text{ A} & I_{B2} &= 1 \text{ A} \\ T_{P} &= 30  \mu \text{s} \text{ (see Figure 14)} \end{split}$			2.5 300	µs ns
E <sub>ar</sub>	Avalanche energy	$\label{eq:L} \begin{array}{ll} {\sf L} = 2 \mbox{ mH} & {\sf C} = 1.8 \mbox{ nF} \\ {\sf I}_{BR} \le 2.5 \mbox{ A} & 25 \mbox{ °C} < {\sf T}_{C} < 125 \mbox{ °C} \\ (see \mbox{ Figure 12}) \end{array}$	6			mJ

1. Pulse test: pulse duration  $\leq$  300 µs, duty cycle  $\leq$  2 %.



#### **Typical characteristics (curves)** 2.1



<sup>4</sup> <sup>6</sup> <sup>8</sup> 10<sup>-1</sup>

6

10°

 $I_{c}(A)$ 

10<sup>-2</sup>



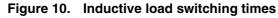
 $10^{-2}$ 

 $10^{-1}$ 

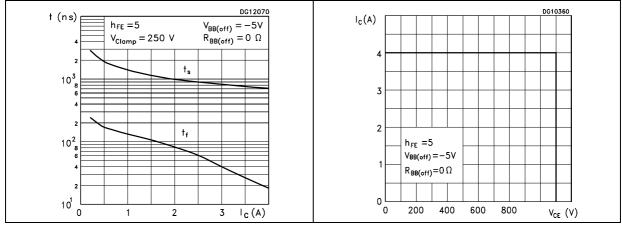
10<sup>0</sup>

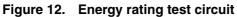
 $I_{c}(A)$ 

Figure 8. Base emitter saturation voltage	Figure 9. Resistive load switching times
$V_{BE (set)}$ 0.9 0.9 0.8 0.7 0.6 0.5 0.6 0.5 0.4 0.3 10 <sup>-2<sup>2</sup></sup> 4 6 <sup>8</sup> 10 <sup>-1<sup>2</sup></sup> 4 6 <sup>8</sup> 10 <sup>9<sup>2</sup></sup> 4 6 <sup>8</sup> (A)	t (ns) f(









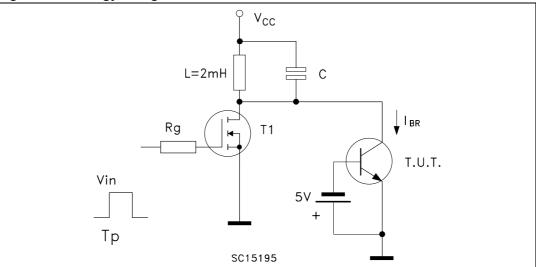
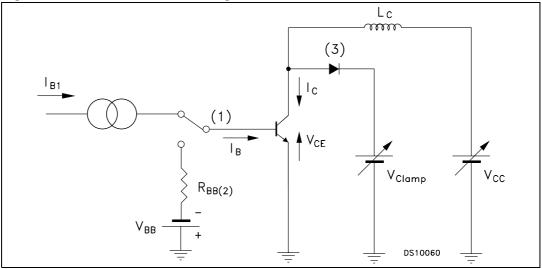
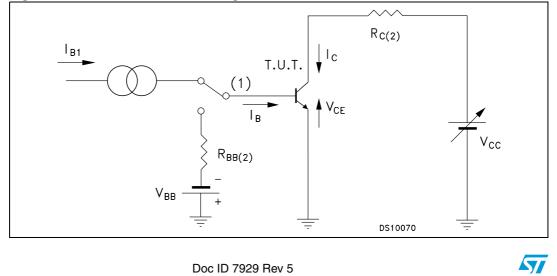


Figure 13. Inductive load switching test circuit







### 3 Package mechanical data

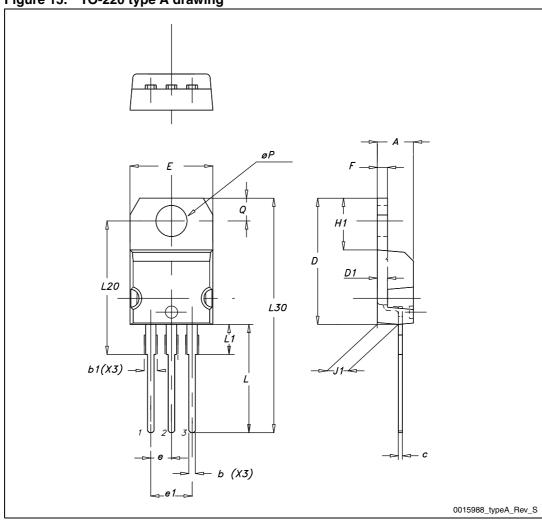
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Table 5.TO-220 type A mechanical data

Dim		mm			
Dim.	Min.	Тур.	Max.		
A	4.40		4.60		
b	0.61		0.88		
b1	1.14		1.70		
с	0.48		0.70		
D	15.25		15.75		
D1		1.27			
E	10		10.40		
е	2.40		2.70		
e1	4.95		5.15		
F	1.23		1.32		
H1	6.20		6.60		
J1	2.40		2.72		
L	13		14		
L1	3.50		3.93		
L20		16.40			
L30		28.90			
ØР	3.75		3.85		
Q	2.65		2.95		





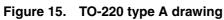




Table 6. TO-220FP mechanical data

Dim.	mm			
Dim.	Min.	Тур.	Max.	
A	4.4		4.6	
В	2.5		2.7	
D	2.5		2.75	
E	0.45		0.7	
F	0.75		1	
F1	1.15		1.70	
F2	1.15		1.70	
G	4.95		5.2	
G1	2.4		2.7	
н	10		10.4	
L2		16		
L3	28.6		30.6	
L4	9.8		10.6	
L5	2.9		3.6	
L6	15.9		16.4	
L7	9		9.3	
Dia	3		3.2	



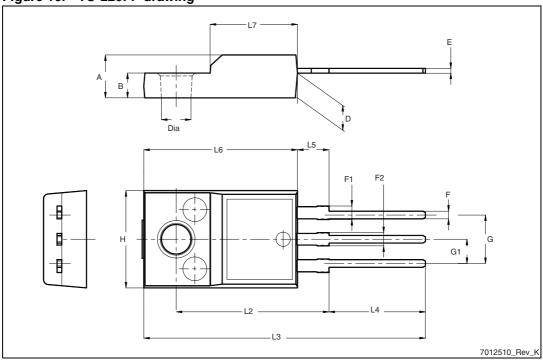


Figure 16. TO-220FP drawing



# 4 Revision history

Table 7.Document revision history

Date	Revision	Changes
17-Jan-2008	3	
24-Mar-2011	4	Inserted BUL1102EFP order code in TO-220FP package
15-Feb-2012	5	DC current gain values in Table 4 modified



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